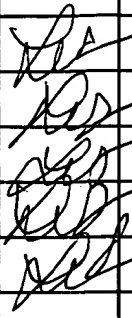
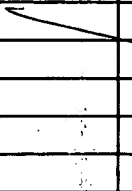
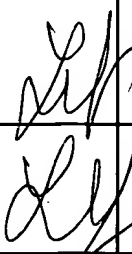
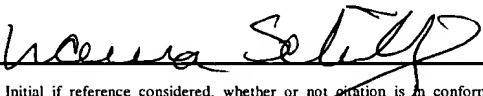
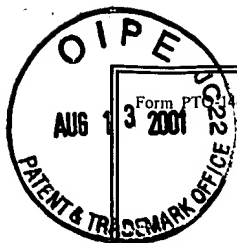


Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1780	PRIORITY SERIAL NO. 09/837,645		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.			
				PRIORITY FILING DATE April 17, 2001	PRIORITY GROUP 2813		
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>[Handwritten initials: R, A, C, A, A, A, A, A, A, A]</i>	AA	5,320,975	6/1994	Cederbaum et al.	437	44	
	AB	5,334,861	8/1994	Pfiester et al.	257	67	
	AC	5,373,170	12/1994	Pfiester et al.	257	69	
	AD	5,411,909	5/1995	Manning et al.	437	52	
	AE	5,418,393	5,1995	Hayden	257	347	
	AF	4,945,065	7/31/90	Gregory, et al.	437	4	
	AG	5,212,108	5/18/93	Liu, et al.	437	60	
	AH	5,523,240	6/4/96	Zhang, et al.	437	21	
	AI	5,726,096	3/98	Jung	438	592	
	AJ	4,569,697	7/86	Tsu et al.			
AK	5,665,611	9/97	Sandhu et al.	438	162		
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<i>[Handwritten initials: R, A, A]</i>	AL	281054A1	7/90	Germany - Mende, et al.			
	AM						
	AP						
OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)							
<i>[Handwritten initials: R, A, A]</i>	AR		Pollack, G.P. et al., "Hydrogen Passivation of Polysilicon MOSFET's From A Plasma Nitride Source", IEEE, 1984 pp. 408-410				
	AS		Kamins, T.I., "Hydrogenation of Transistors Fabricated in Polycrystalline-Silicon Films", IEEE, 1980, pp. 159-161				
	AT		Seager, C.H. et al., "Studies of the hydrogen passivation of silicon grain boundaries", J.Appl. Phys. 52, February 1981, pp. 1050-1055				
EXAMINER <i>[Signature: Hanna Schuler]</i>				DATE CONSIDERED <i>[Handwritten: 11/17/01]</i>			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1780	PRIORITY SERIAL NO. 09/837,645		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.			
				PRIORITY FILING DATE April 17, 2001	PRIORITY GROUP 2813		
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	5,605,848	2/97	Ngaoaram			
	AB	5,364,803	11/94	Lur et al.			
	AC	5,830,802	11/98	Tseng et al.	438	592	
	AD	5,372,860	12/94	Fehlner et al.	427	578	
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	AF						
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	AH						
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AK							
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	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
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	AR	Kitajima, H. et al., "Leakage Current Reduction in Sub-Micron Channel Poly-Si TFTs", Extended Abstract - 1991 International Conference on Solid State Devices and Materials, Yokohama, 1991, pp. 174-176					
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<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							



Sheet 1 of 1 # 3  
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Form PTO-149

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AA	5,753,543	5/19/98	Sandhu et al.	438	163	
AB	6,001,675	12/14/99	Sandhu et al.	438	151	
AC	6,077,732	6/20/00	Sandhu et al.	438	158	
AD	6,238,957	5/29/01	Sandhu et al.	438	151	
AE						
AF						
AG						
AH						
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AJ						
AK						
AL						

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
AM							
AN							
AO							
AP							
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